

L Number	Hits	Search Text	DB	Time stamp
1	1	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first) and photodiode and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:55
2	5	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:58
3	21	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:59
4	1	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and photodiode and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:04
7	3	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:10
8	21	(high with voltage with well) and (low with voltage with well) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:35
9	1	(high adj voltage adj well) and (low adj voltage adj well) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:11
10	2	cmos same dmos same mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:04
11	10	cmos and dmos and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:05
12	2420	mem same (accelerometer or sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
13	2420	mems same (accelerometer or sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
14	1862	mems with (accelerometer or sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
15	509	mems with accelerometer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
16	2	cmos same dmos same photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:18
17	16	cmos and dmos and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:05
18	31	cmos same dmos same soi	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:18
41	2	5578506.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:30

46	2	5681761.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:30
47	113	(high with voltage with well) and (low with voltage with well) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:36
48	104	((high with voltage with well) and (low with voltage with well) and photodiode) and @ad<20020222	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:47
49	1	(high adj voltage adj well) and (low adj voltage adj well) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:37
50	71986	photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:48
51	67	photodiode and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:48
-	3203	438/22\$1.cccls. or 438/518.cccls. or 438/519.cccls. or 438/527.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
-	18	(438/22\$1.cccls. or 438/518.cccls. or 438/519.cccls. or 438/527.cccls.) and (high with voltage with (n adj well)) and (low with voltage with (p adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 17:46
-	1	(sixth adj mask\$3) and (high with voltage with (n adj well)) and (low with voltage with (p adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:21
-	70	(438/22\$1.cccls. or 438/518.cccls. or 438/519.cccls. or 438/527.cccls.) and (high with voltage with well) and (low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 18:40
-	68	((438/22\$1.cccls. or 438/518.cccls. or 438/519.cccls. or 438/527.cccls.) and (high with voltage with well) and (low with voltage with well)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 17:47
-	324	(high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:55
-	39	((high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)) and (implant\$5 with (p adj (body or region or well)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:29
-	0	20030162375.URPN.	USPAT	2003/12/15 18:43
-	44	257/548.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:13
-	35	((high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)) and (implant\$5 with p with high with voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:29
-	7	((first with mask\$3) same (implant\$5 with high with voltage with well)) and ((second with mask\$3) same (first with low with voltage with well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:57

	2579	high with voltage with well with (implant\$5 or form\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:22
	201	low with voltage with well with (implant\$5 or form\$3) with first	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
	196	low with voltage with well with (implant\$5 or form\$3) with second	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
	114	(high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
	3208	438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:24
	11	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 12:52
	6	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and cmos and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 12:42
	7	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first) and cmos and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 14:16
	8	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (fifth with mask\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 14:16
	144	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 13:13
	131	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 13:13
	1	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (fifth with photoresist with film)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:53